



# **Unique opportunities for new insight in the outer surfaces and interfaces by High Sensitiviy Low Energy Ion Scattering (HS-LEIS)**

Hidde Brongersma

ION-TOF GmbH / Eindhoven University of Technology /  
Imperial College (London)

[H.H.Brongersma@tue.nl](mailto:H.H.Brongersma@tue.nl)

March 23, 2011  
Lehigh University

ION-TOF GmbH  
Heisenbergstr. 15  
D-48149 Münster / Germany  
[www.iontof.com](http://www.iontof.com)

- **Introduction**
- **Principles and features of LEIS**
  - 1st atom, In – depth ( 0 – 10 nm ), quantitative
- **Applications**
  - Organics (surface modif., anti-wetting, SAMs)
  - Catalysts (mixed oxides, coke, NP's, oxid. states)
  - Ceramics (SOFC, membranes)
  - ALD growth (high-k, inter-diffusion)
  - and many more .....

# Why High-Sensitivity LEIS ?

ionTOF

CONTROL at the ATOMIC LEVEL

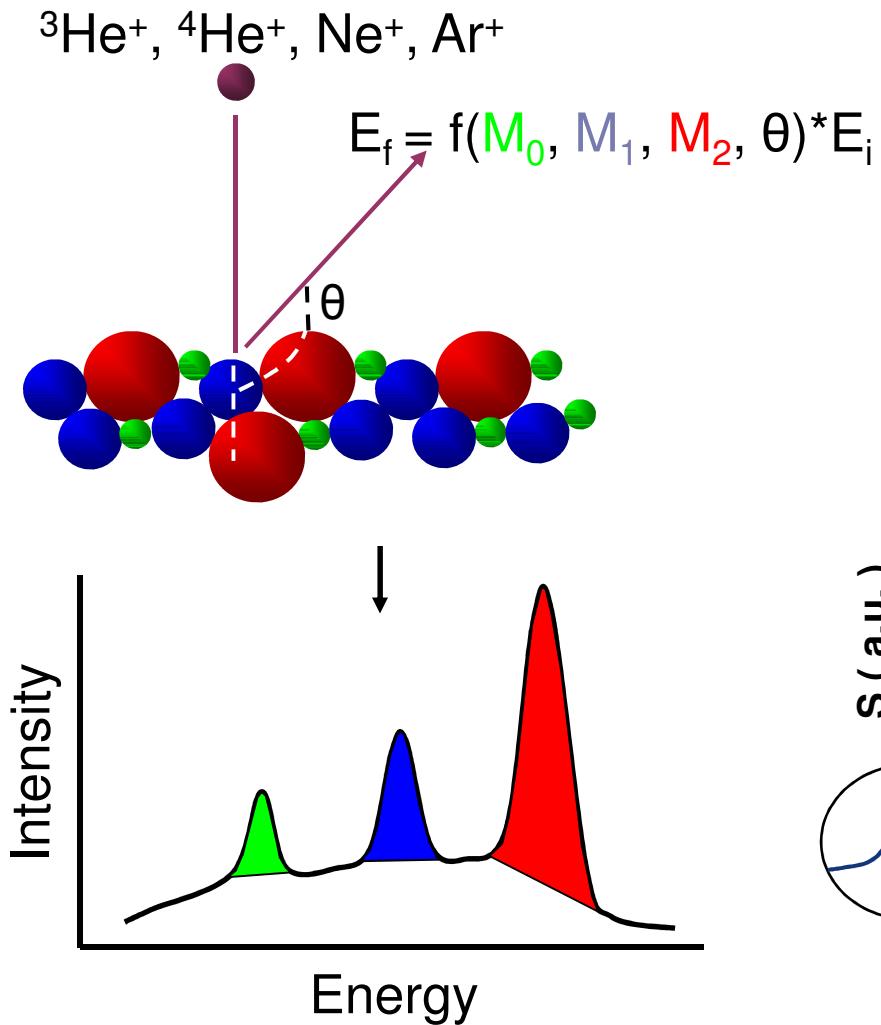
requires

QUANTITATIVE ANALYSIS at the ATOMIC LEVEL

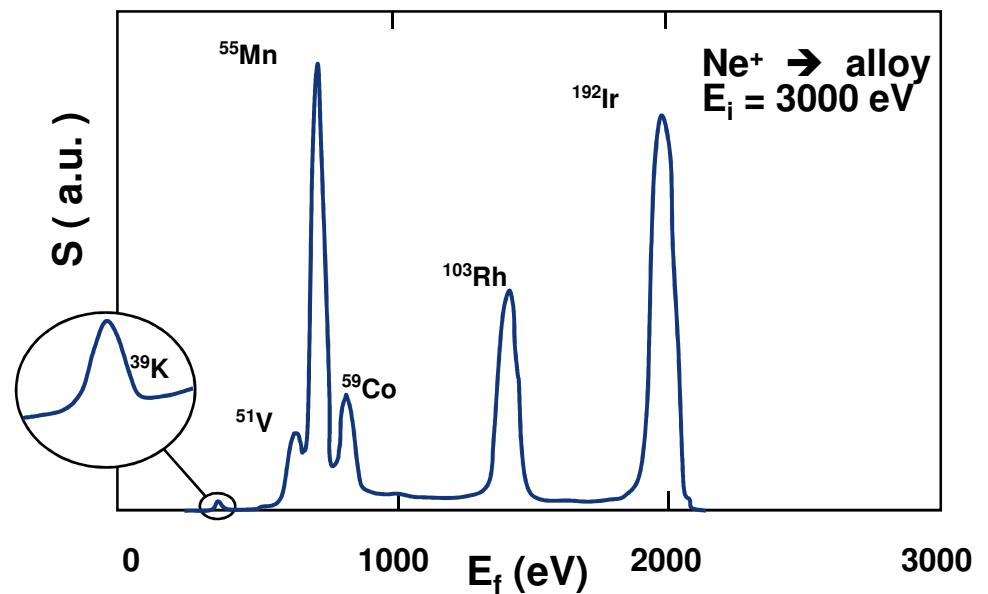
# Low Energy Ion Scattering

ionTOF

## Analytical Capabilities



- Atomic composition of the outermost atomic layer
- Energy 1 – 8 keV
- Lateral resolution 0.01 – 1 mm
- Static in-depth (0 – 10 nm)
- Quantitative !!
- No matrix effects

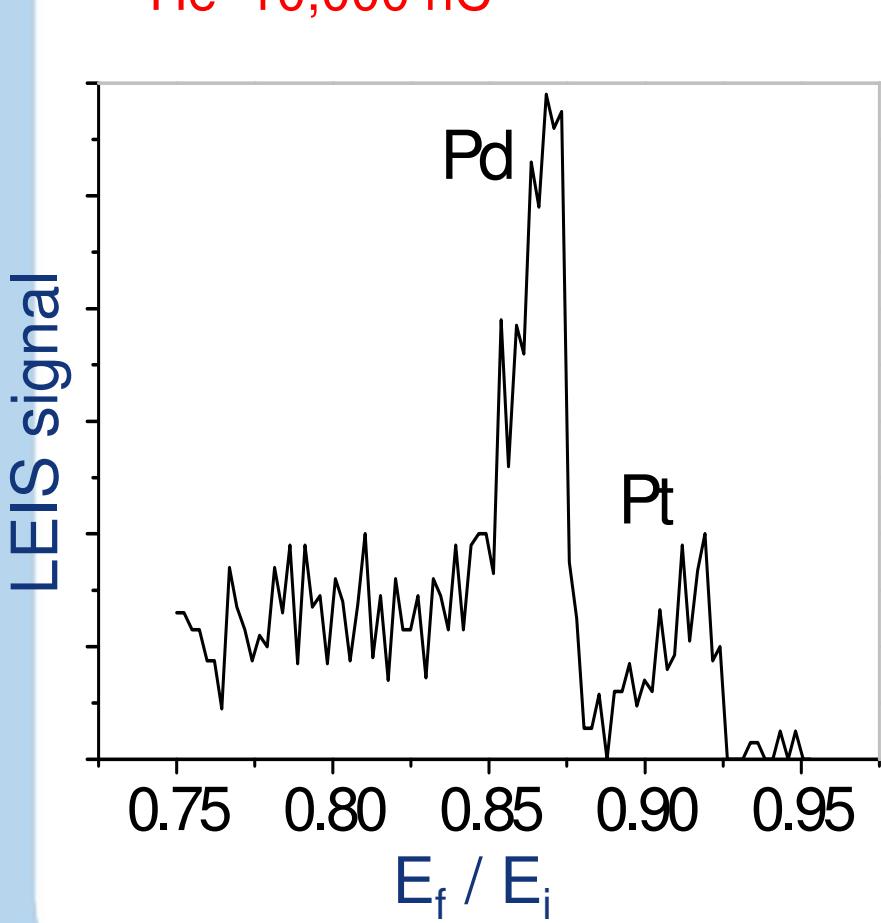


# Conventional LEIS vs HS - LEIS

ionTOF

Pd / Pt-C ( 1000 m<sup>2</sup>/g )

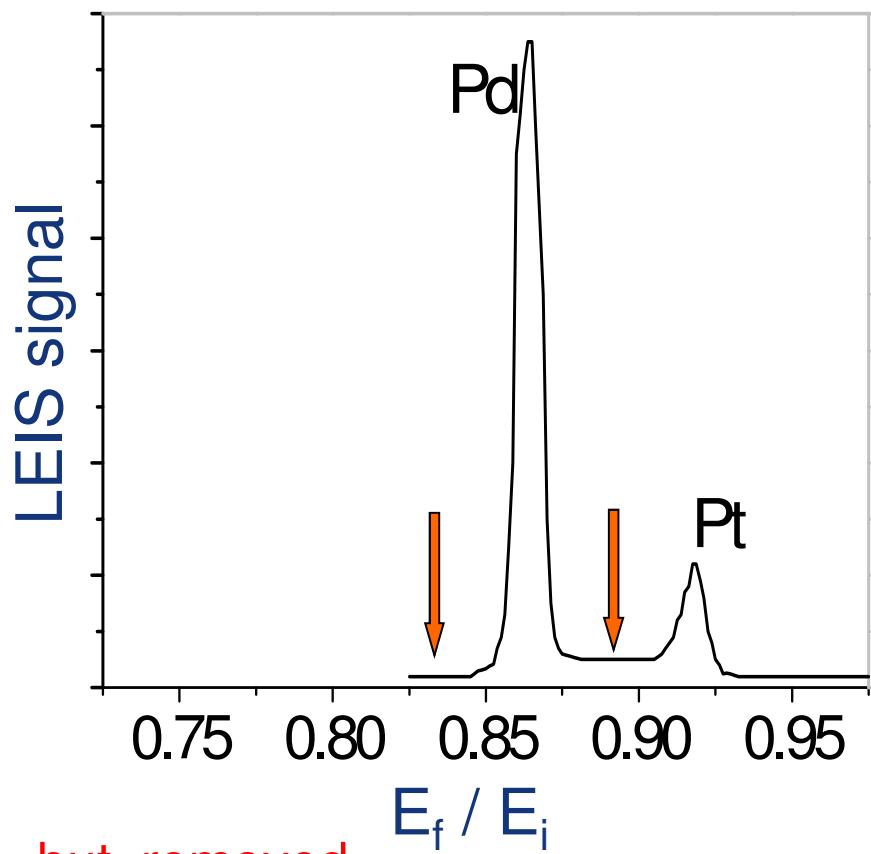
Conventional



NIM B 68 (1992) 207

High-Sensitivity LEIS

${}^4\text{He}$  5.4 nC



Promoters visible, but removed

# Qtac : Unique new Analyser

ionTOF

## High – Sensitivity LEIS

Energy image:

- parallel energy detection
- only low dose needed



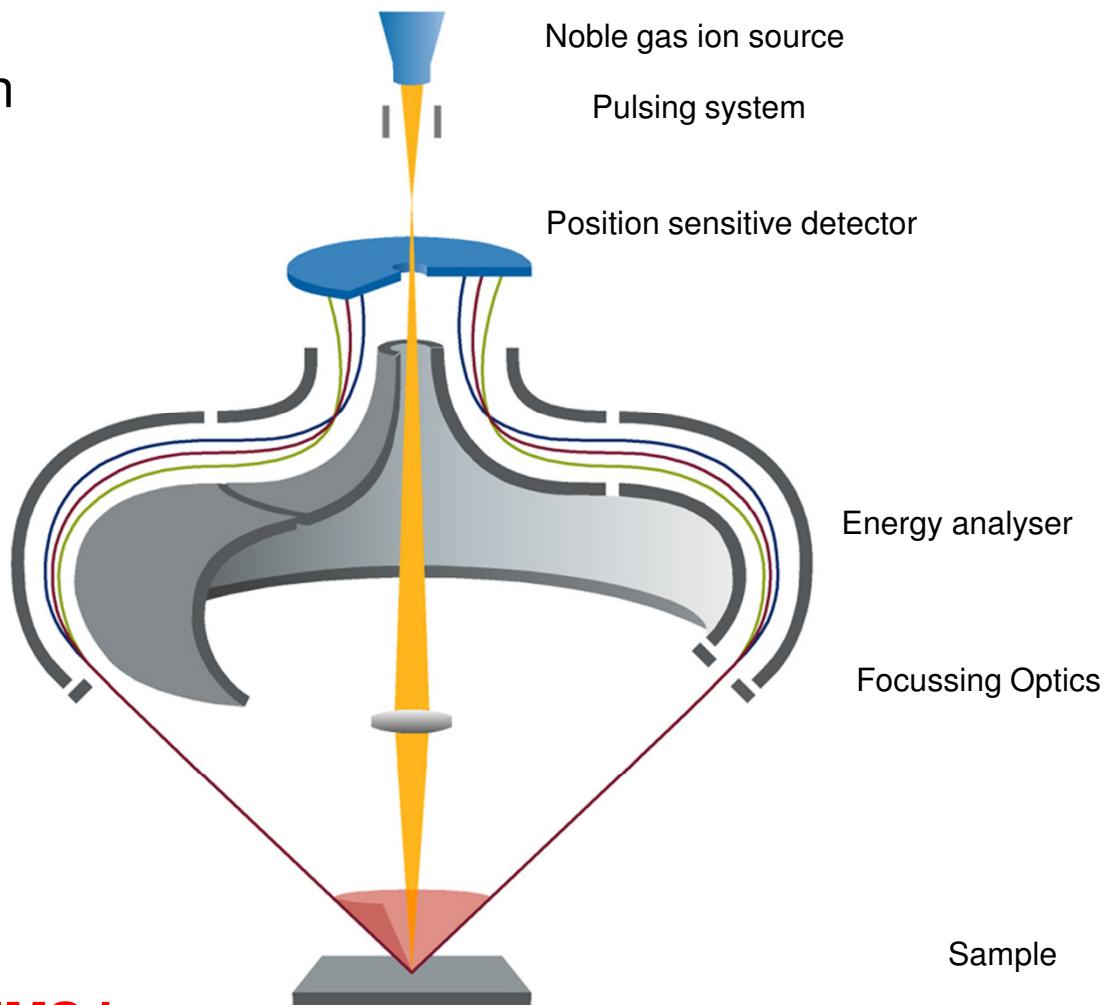
**STATIC LEIS**

“ Analysis **before** Damage ”

(Molecular Dynamics  
simulation)

“ Hit same place only once ”

**ToF filtering eliminates SIMS ions**



- Analysis *before* damage (static)
- 1<sup>st</sup> Monolayer
- Quantitative (peak → concentration / coverage)
- Sensitivity
- Mass resolution
- ToF-filtered LEIS
- Imaging

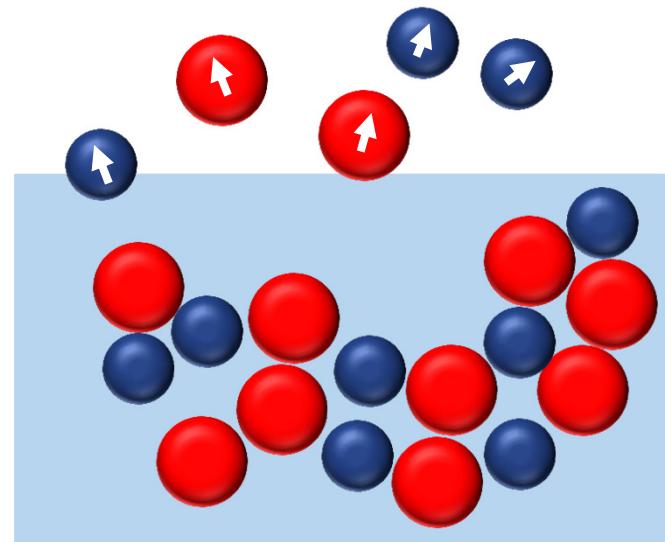
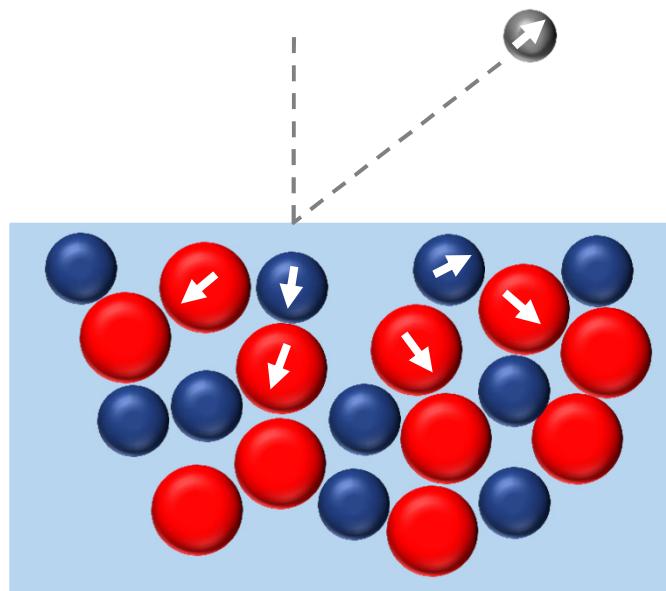
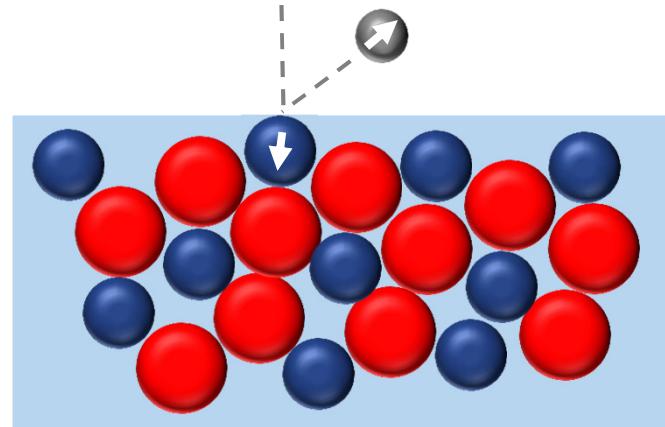
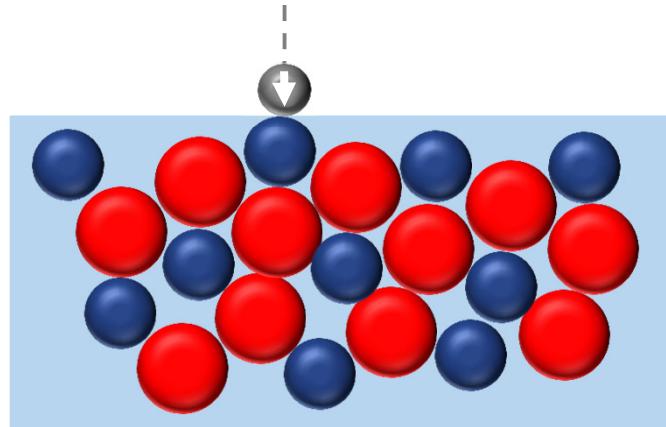
---

- In-depth: Static (0 – 6 nm) *or* with sputtering

# LEIS and SIMS

ionTOF

Time resolved: LEIS analysis *before* damage !



LEIS

SIMS



# Quantification

Review:

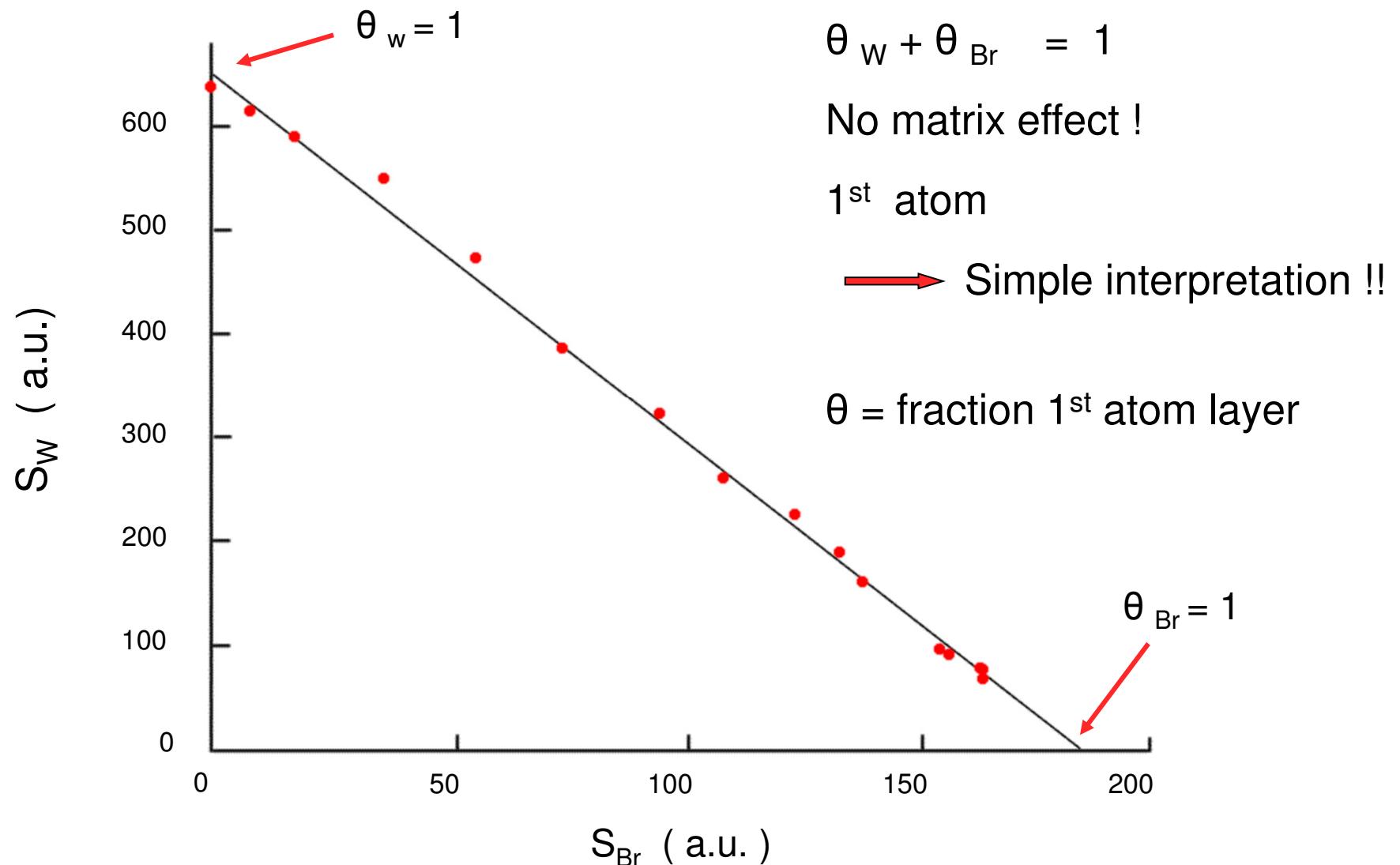
Brongersma et al., Surf. Sci. Reports, 62 (2007) 63 – 109.

ION-TOF GmbH  
Heisenbergstr. 15  
D-48149 Münster / Germany  
[www.iontof.com](http://www.iontof.com)

# Quantification

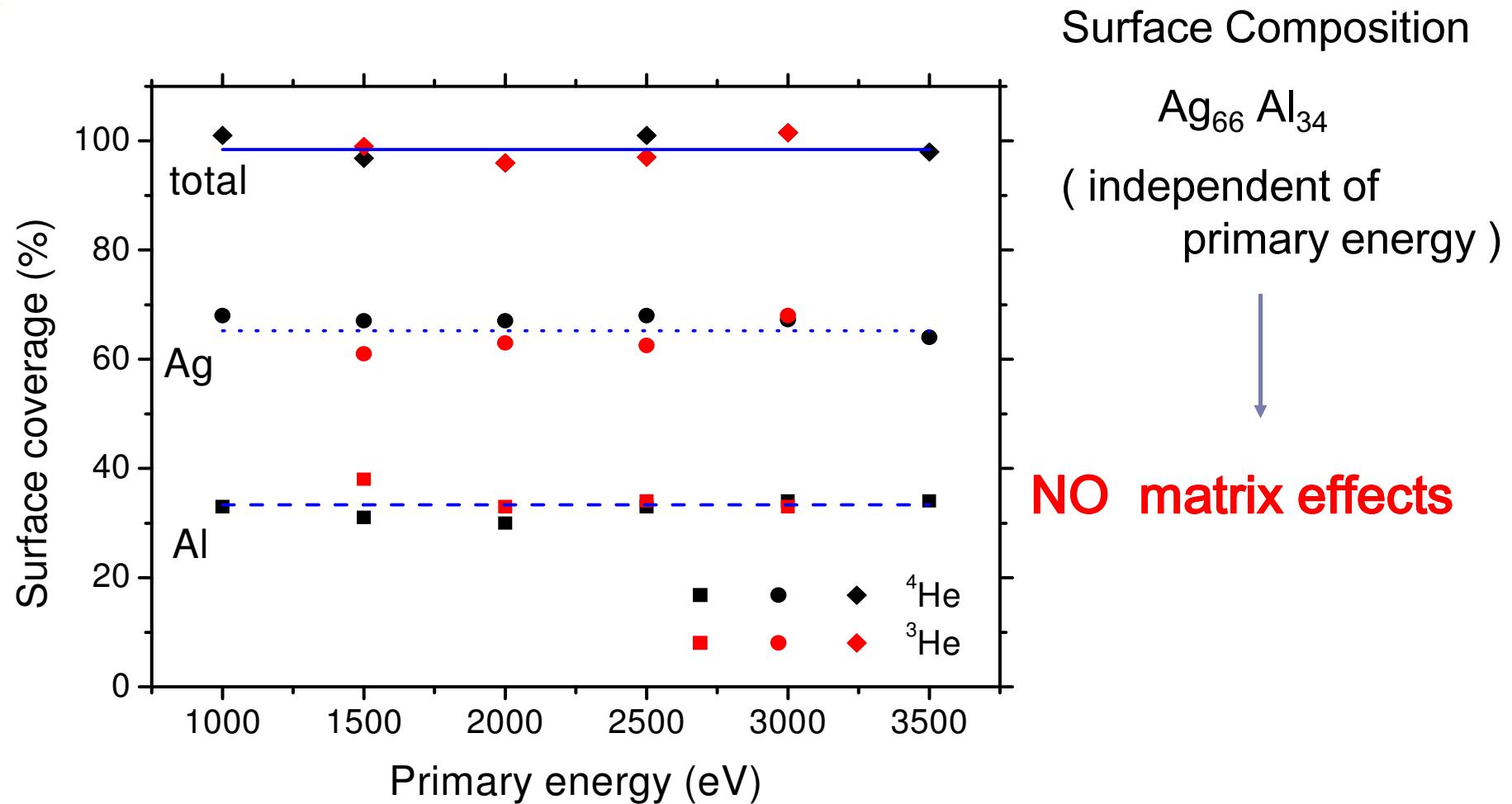
ionTOF

## Bromine adsorption on Tungsten



# Bulk Composition $\text{Ag}_{80}\text{Al}_{20}$

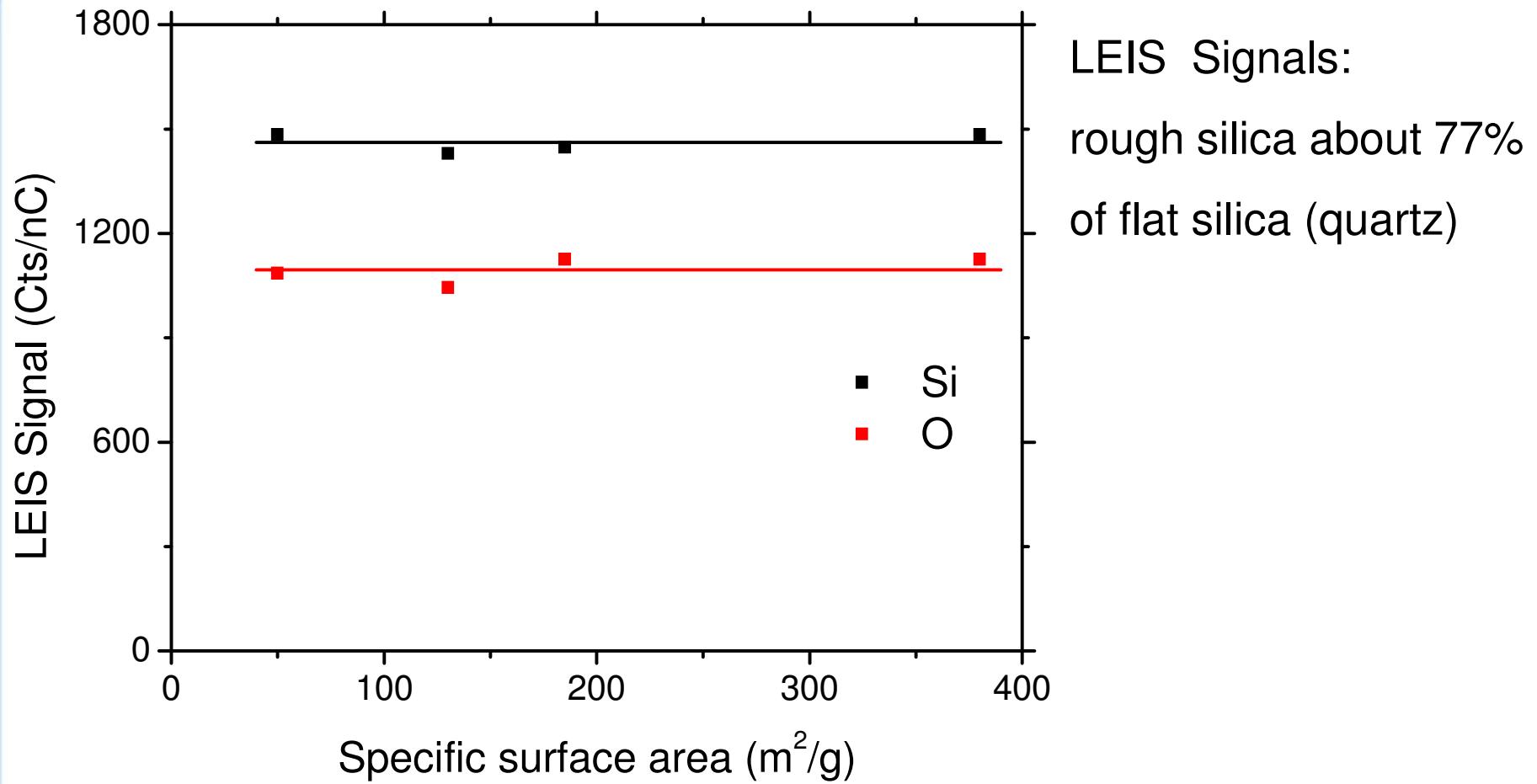
ionTOF



Rough silica: 50 – 380 m<sup>2</sup>/g

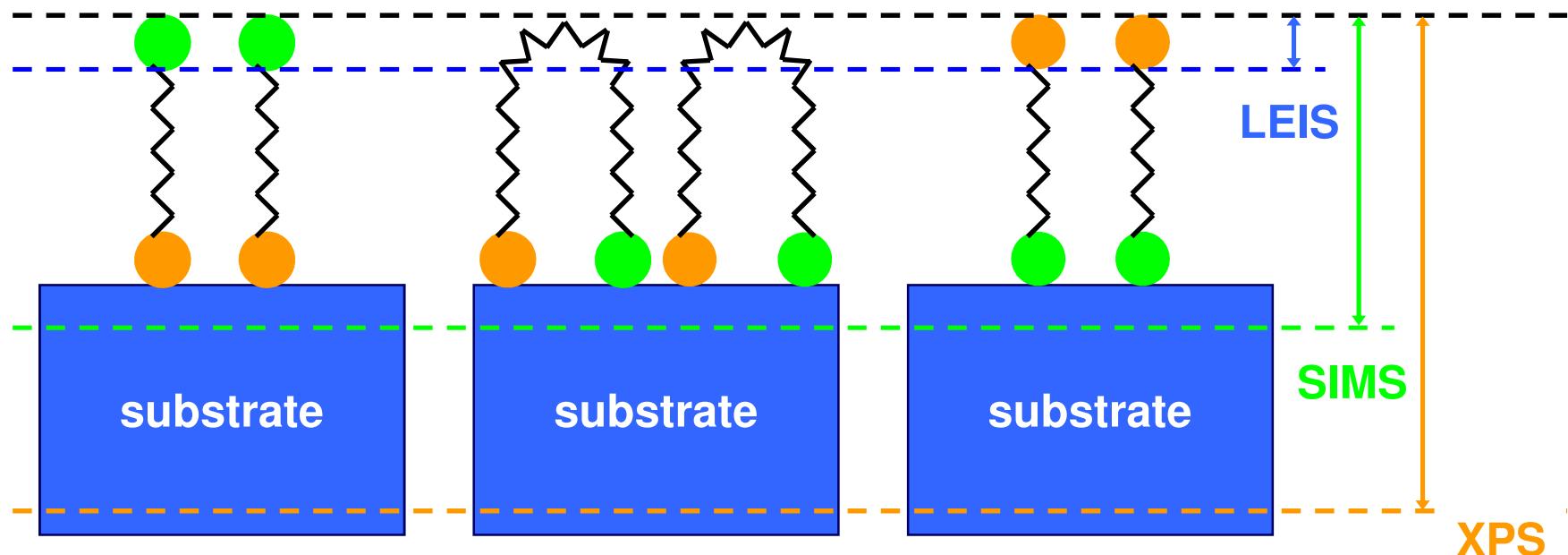
ionTOF

HS-LEIS: Insensitive to roughness



# Monolayer sensitivity

ionTOF



**LEIS** 1<sup>st</sup> atom and in-depth; quantitative, sensitive

**SIMS** not quantitative for near-surface / interface

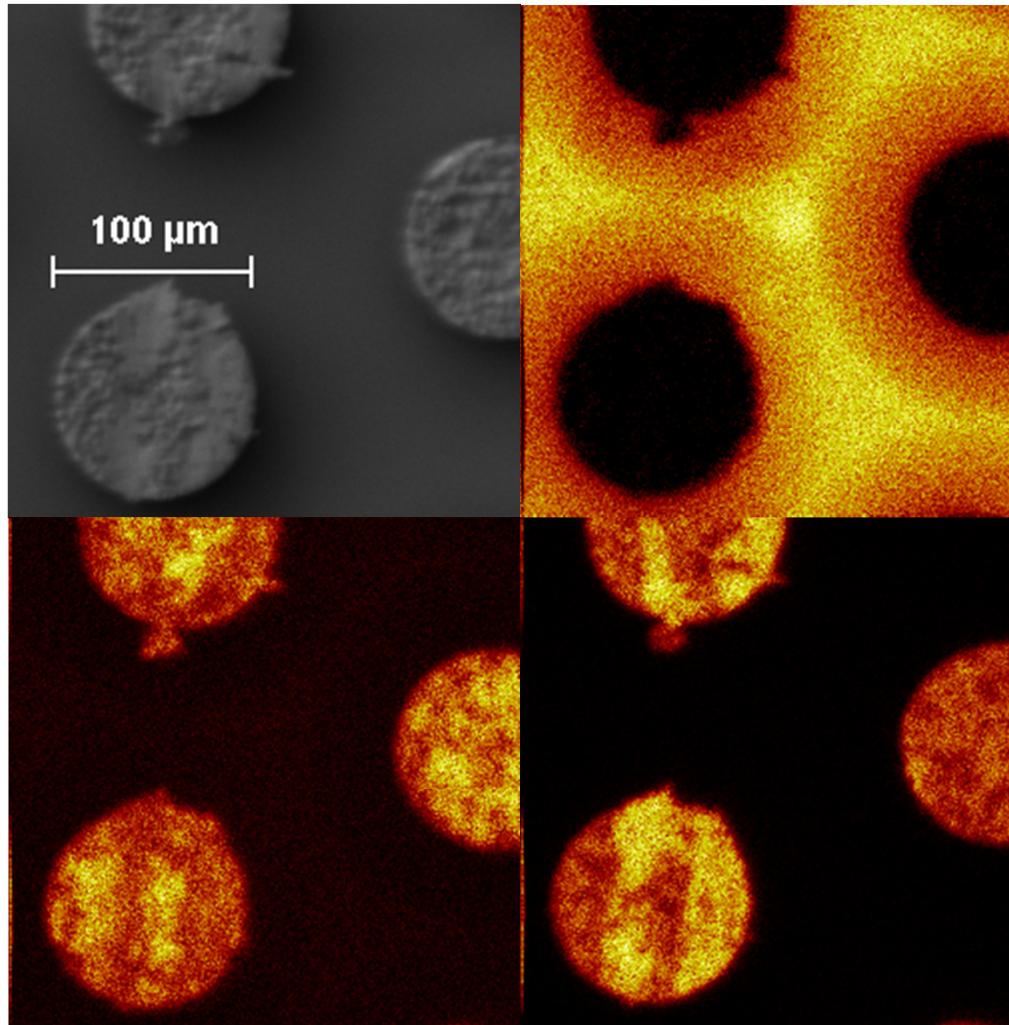
**XPS** average over 3 – 10 nm; chemical info

# Elemental mapping by LEIS and SE Image

## Solder bumps

ionTOF

SE image



# LEIS and Microelectronics



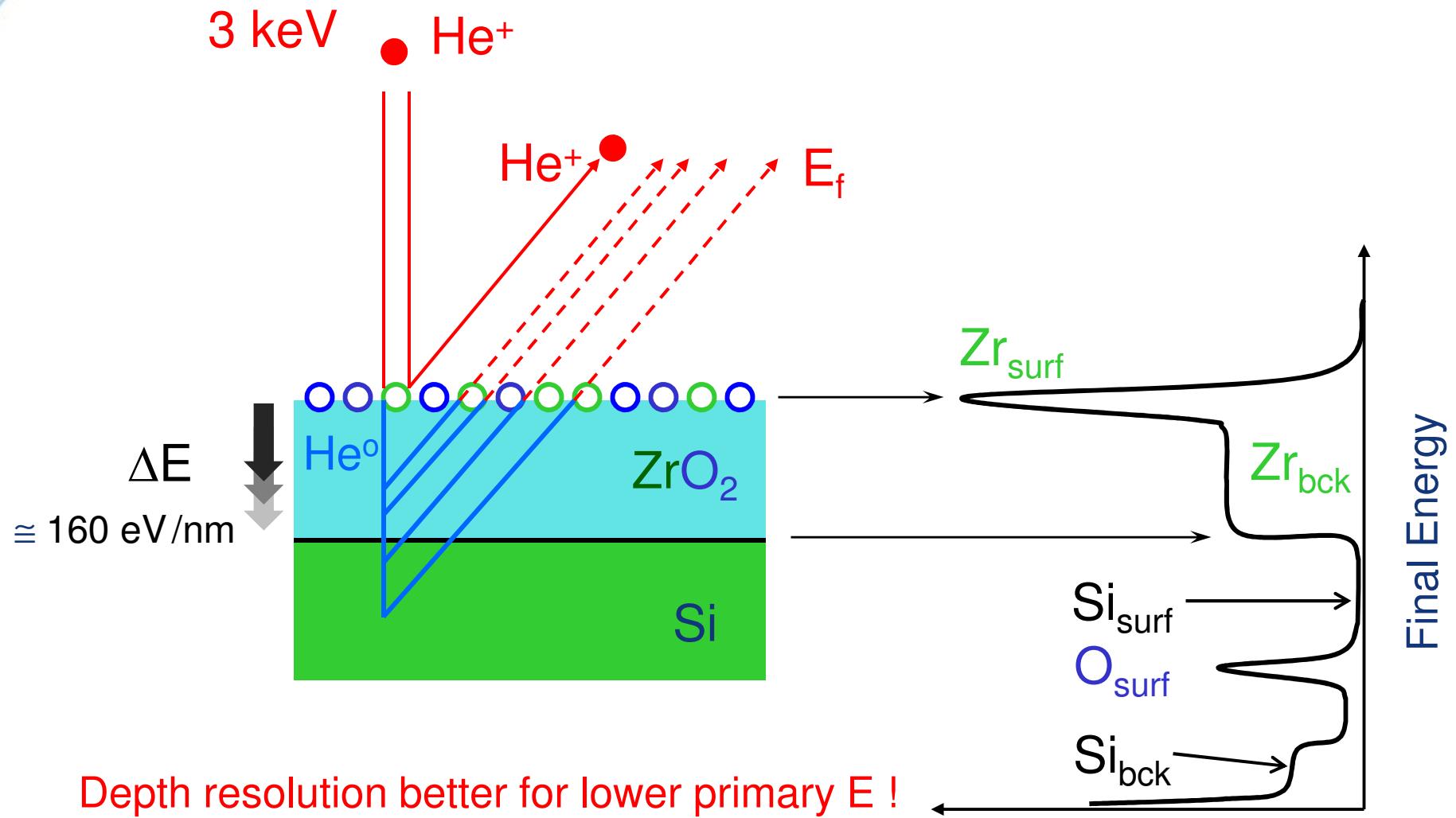
Depth info for  
Ultra thin layers and interfaces

## Two possibilities:

1. Static LEIS + sputter depth profiling with dual ion beam  
(advantage of quantification, depth resolution LEIS)
2. Static LEIS  
(analogous to RBS and MEIS, but better depth resolution)

# Depth info

ionTOF

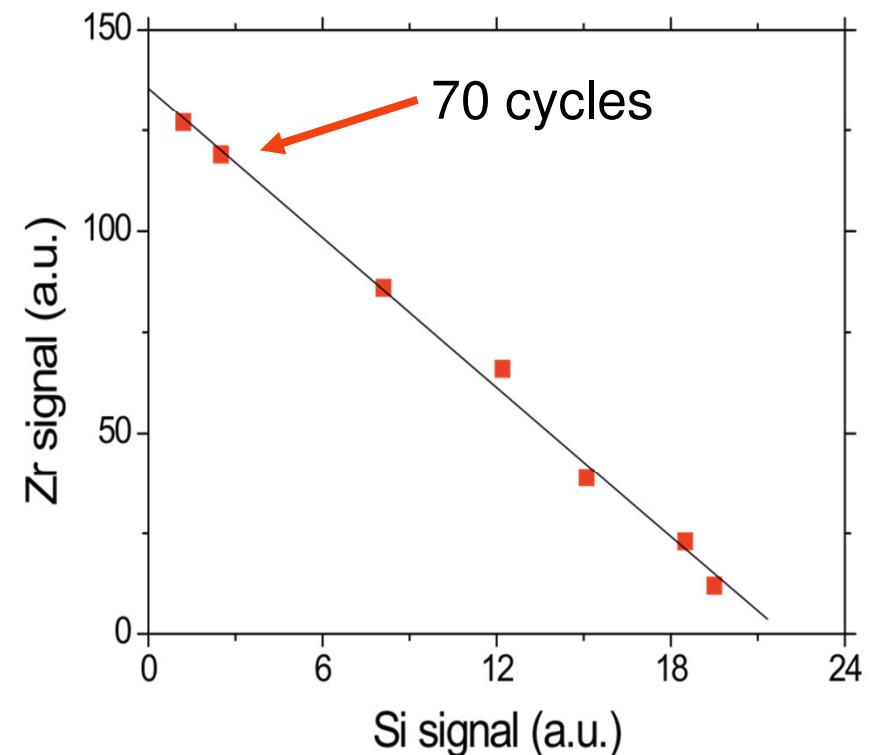
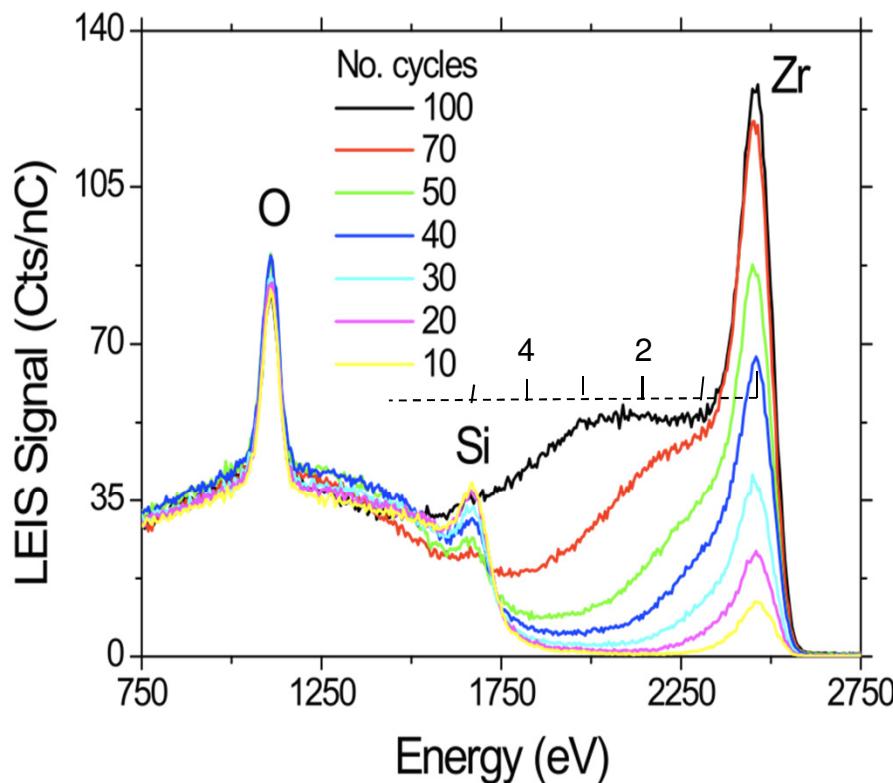


# 1<sup>st</sup> atom and Static Depth Profile

ionTOF

## ZrO<sub>2</sub> Atomic Layer Deposition on Silicon

- Closure / quantification pinholes (still present after 70 cycles)
- Thickness distribution ZrO<sub>2</sub> layer (160 eV/nm)
- No matrix effect
- Example: calibration / quantification for a 2 component system



In LEIS only backscattered *ions* are detected

**Peaks:** Ions backscattered from 1<sup>st</sup> atom.  
(*one well-defined* collision)

**Tails:** Backscattering in deeper layers + reionization  
(Scattering by oxygen atoms: efficient reionization)

→ Shape:  $f$  ( in-depth distribution Zr )

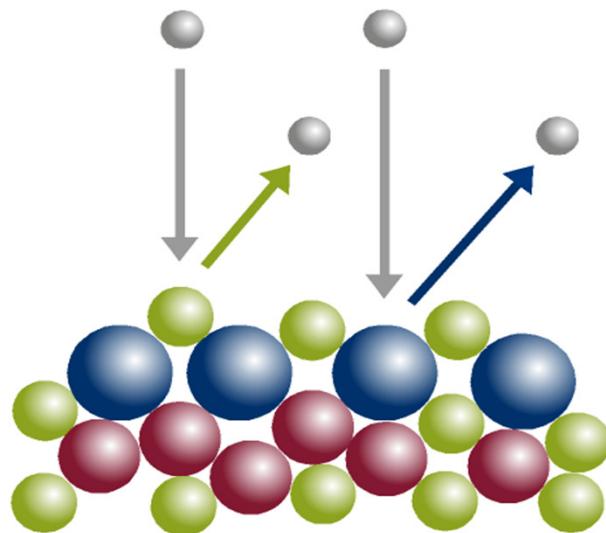
Intensity:  $f$  ( oxygen concentration in  
1<sup>st</sup> atomic layer )

# LEIS Technique

ionTOF

## Features of Low Energy Ion Scattering (LEIS)

$\text{He}^+$ ,  $\text{Ne}^+$ ,  $\text{Ar}^+$ ,  $\text{Kr}^+$   
1 - 8 keV



### LEIS Features

Ultra-high surface sensitivity,  
***top atomic layer*** analysis  
***Static*** depth profiling information (up to 10 nm)

Reliable and straight-forward ***quantification***

Detection of all elements  $> \text{He}$

Detection limits:

$\text{Li} - \text{O} \geq 1\% \text{ of } 1 \text{ ML}$

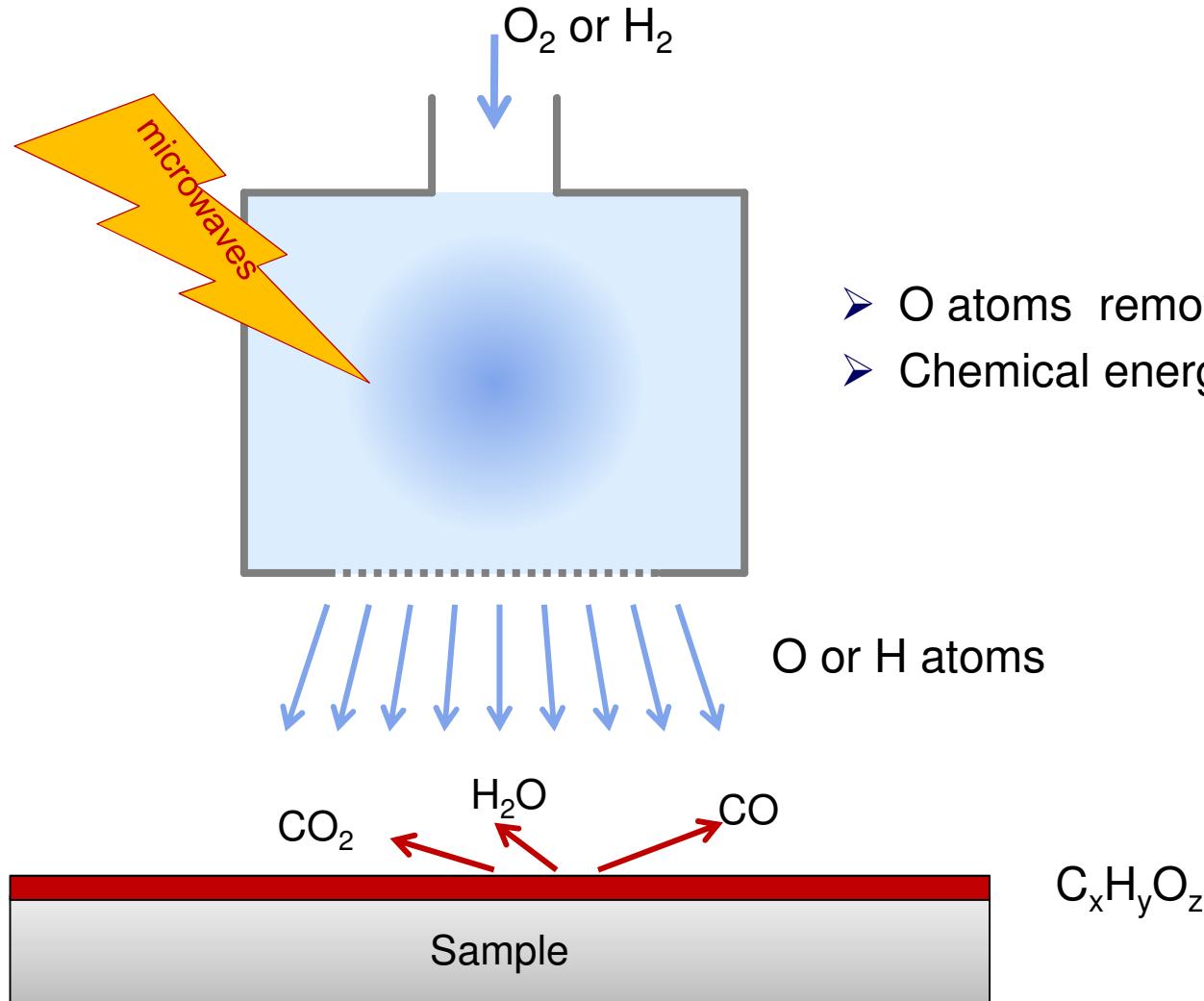
$\text{F} - \text{Cl} 1\% - 0.05\% \text{ of } 1 \text{ ML}$

$\text{K} - \text{U} 500 \text{ ppm} - 10 \text{ ppm} \text{ of } 1 \text{ ML}$

# Sample Treatment

ionTOF

## Atom Source for Surface Cleaning



- O atoms remove organics, coke
- Chemical energy: no sputtering

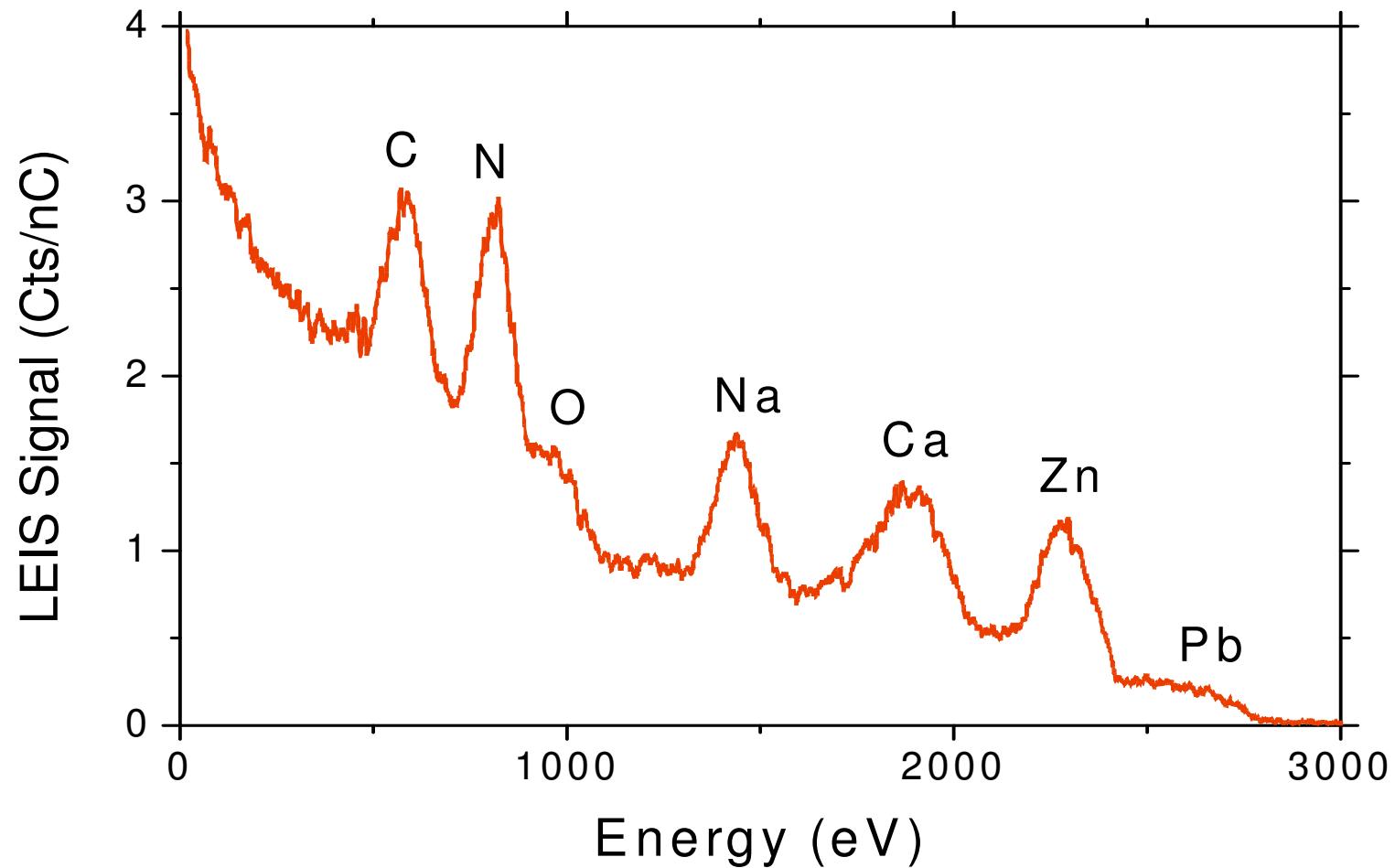
- Surface segregation
- Dendrimers
- Antiwetting
- Surface modification
- Metal / polymer interface
- SAMs

- Inter - molecular segregation
  - Segregation impurities, additives (0.1 s - days - ..;  
up to  $10^8 \times$  !! )
- Intra - molecular segregation (0.1 s - days - ..)
  - Aging plasma oxidized PE
- Anti - wetting layers
- Metal diffusion in polymers
- SAM's

# Acrylonitrile-Butadiene-Styrene (ABS)

ionTOF

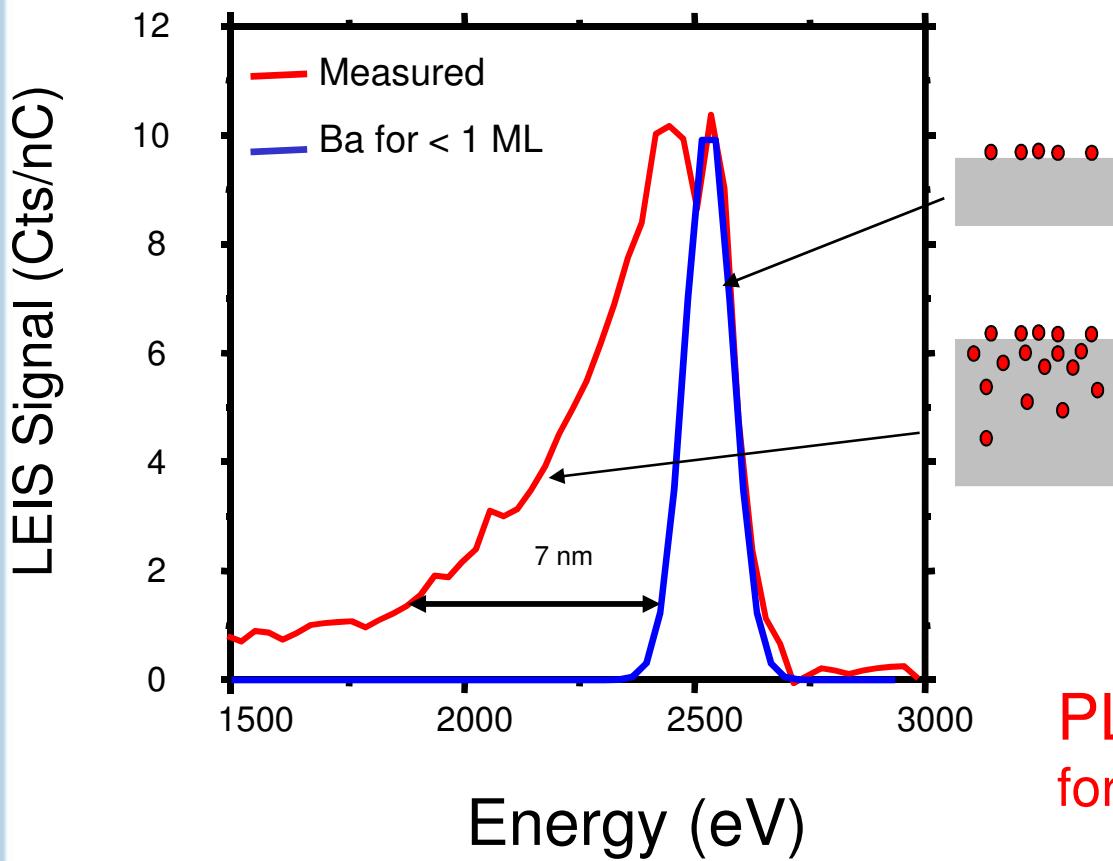
## Surface segregation of additives



# Metal - polymer interface in ultra - thin layers

ionTOF

PLED: Ba evaporation on PPV



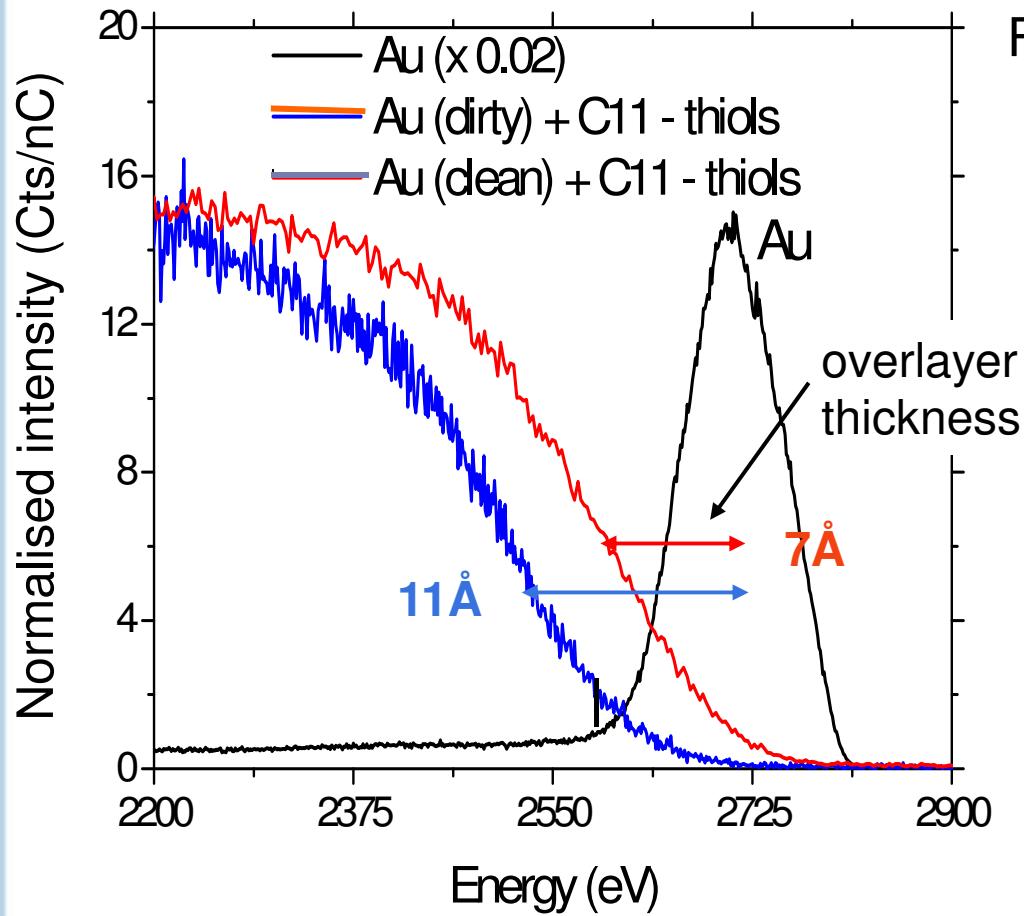
During evaporation of barium on PPV, most of the Ba diffuses into the PPV.

Compare the peakshape of a sub-monolayer of Ba (blue) with the actual peak (red)

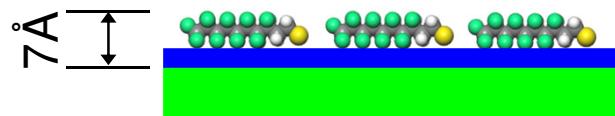
Peak shape  $\leftrightarrow$  depth distribution

PLED: higher light output for narrow depth distribution

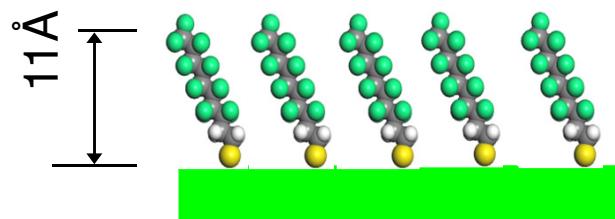
# High-energy edge of SAMs on Au



Fluorinated thiol on **dirty** Au surface



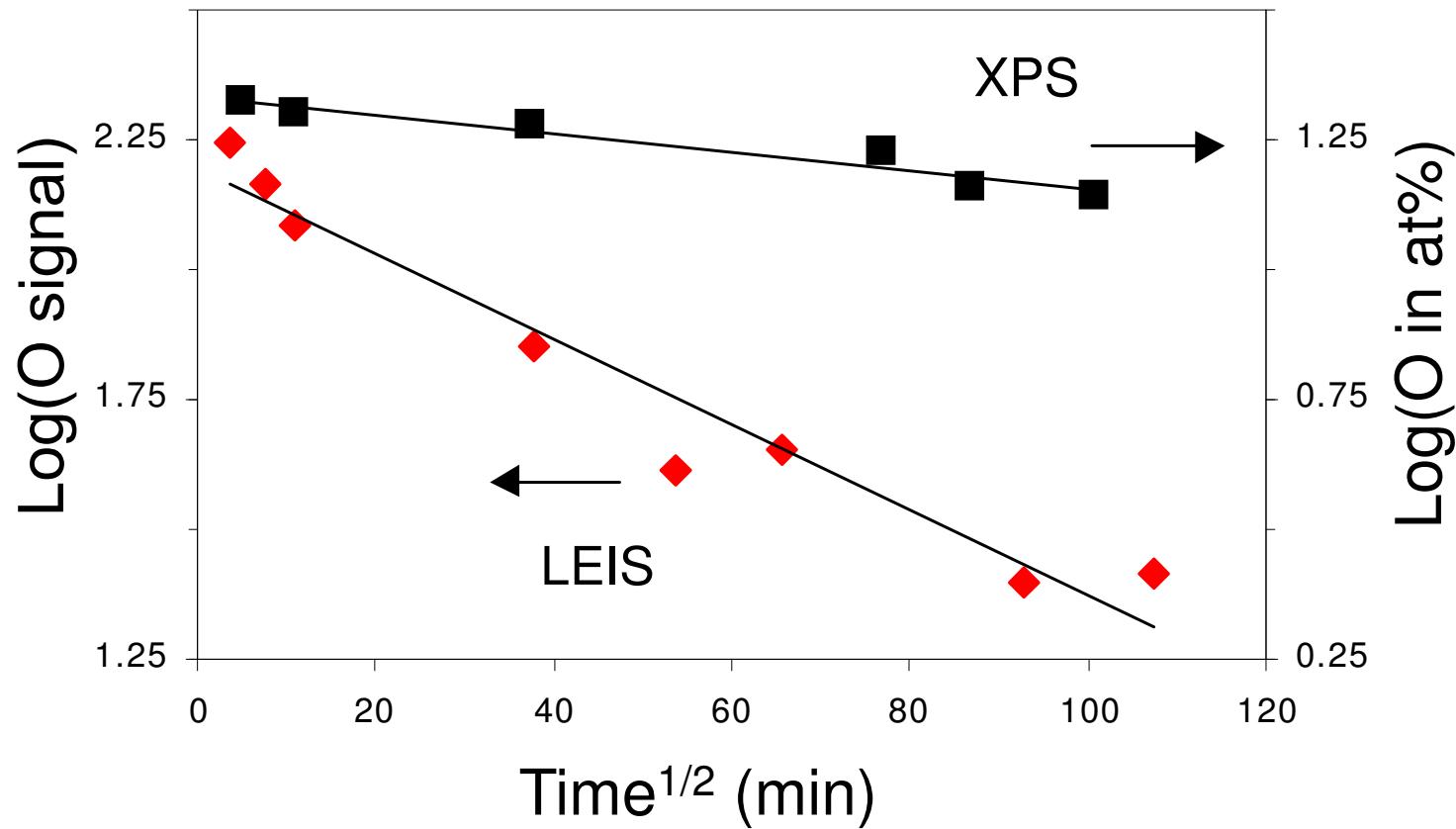
Fluorinated thiol on **clean** Au surface



# Aging of plasma oxidized HDPE

ionTOF

- Aging (LEIS) faster than aging (XPS) !
- “Straight line” → diffusion process



## Selection of examples:

- Pt/Au
- Mixed oxides
- $\gamma$ -alumina
- Poison (Coke on TWC)
- Poison (oxygen membranes, SOFC)
- Use of probe molecules
- NP's , core/shell
- Oxidation state 1st atom

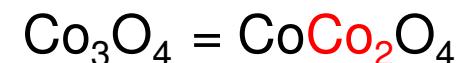
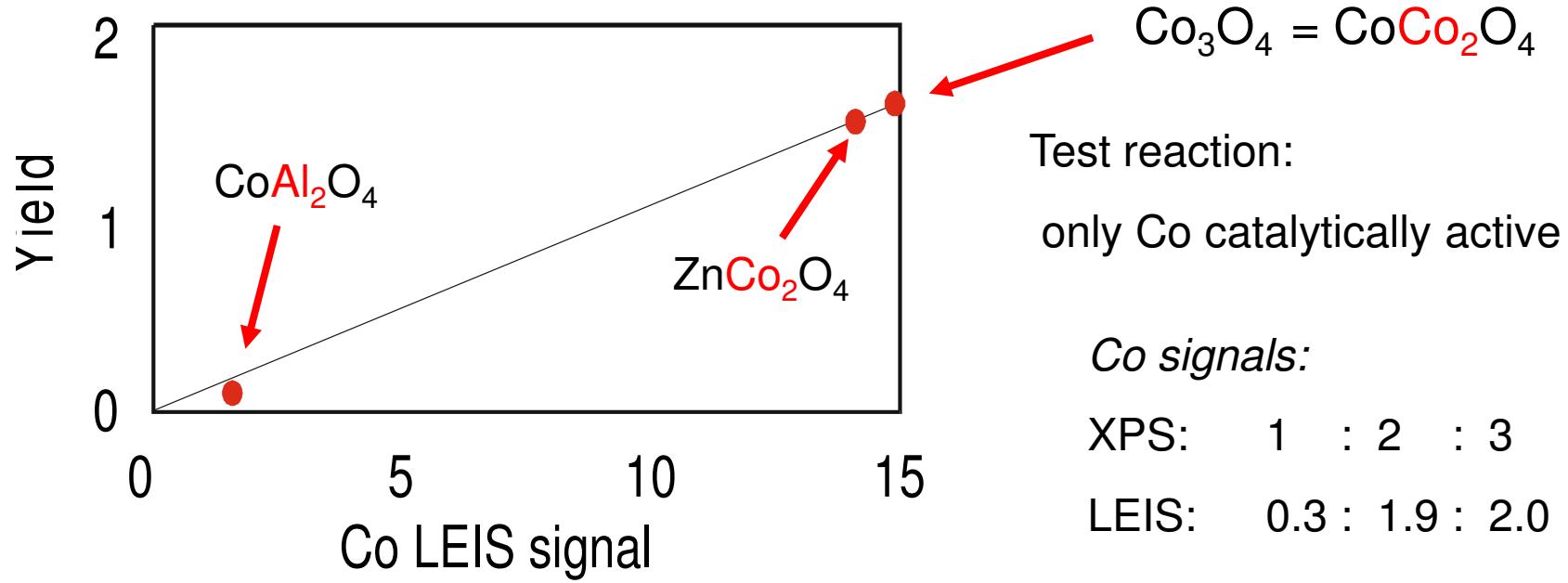
# Important / unique applications for catalysis

## Mixed oxides and catalysis

The atomic composition of the 1<sup>st</sup> atom layer controls catalysis.

In a spinel ( $\text{AB}_2\text{O}_4$ ) only the B-cations (octahedral site) are **catalytically active and visible** for LEIS (1<sup>st</sup> at.).

The A-cations (tetrahedral sites) are in 2<sup>nd</sup> layer (not active, no LEIS peak).



Test reaction:  
only Co catalytically active

Co signals:

XPS: 1 : 2 : 3

LEIS: 0.3 : 1.9 : 2.0

LEIS



Catalysis



XPS

# Fuel Cells and Membranes

ionTOF

## Importance of the outer surface

- Performance relies on oxygen transport
- Performance: “ Hampered by the surface ”
- Why ? What is the surface ??

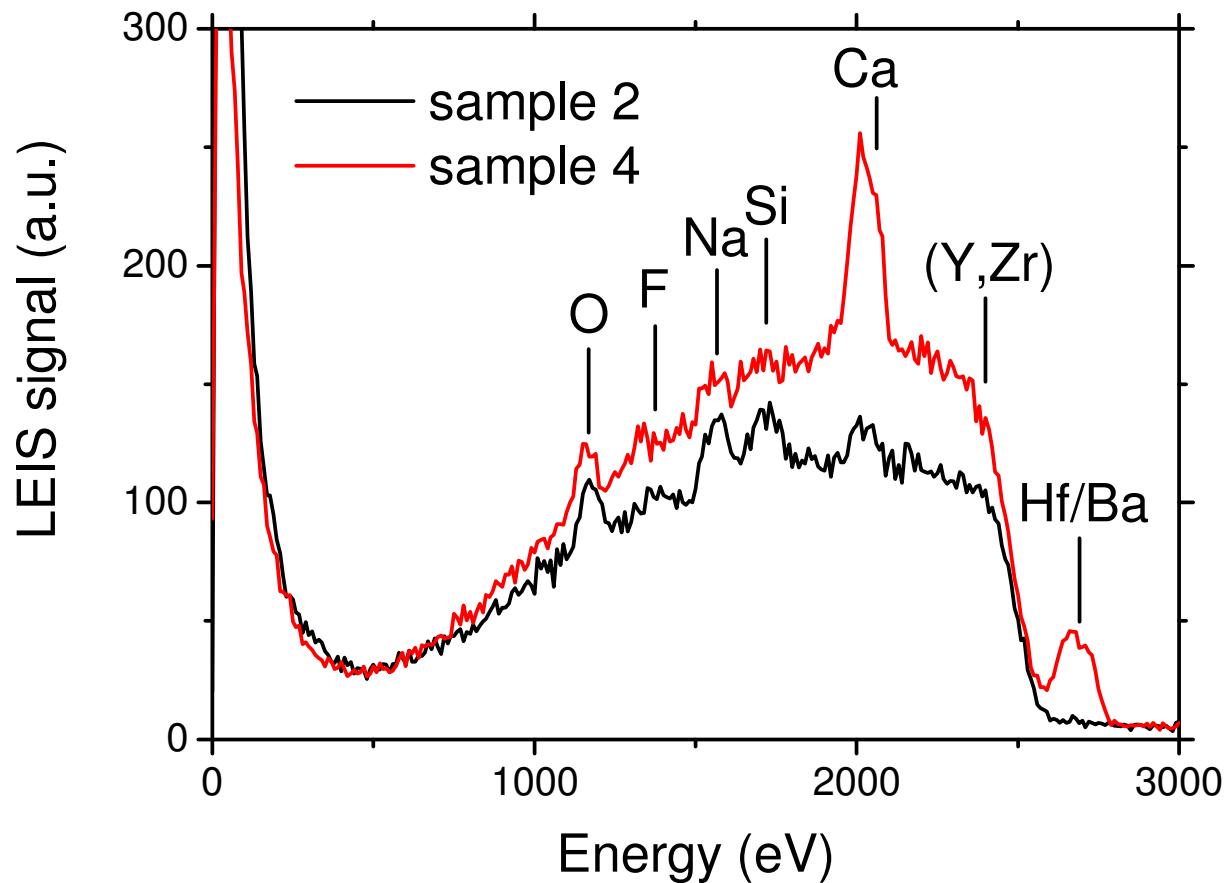
M. de Ridder et al., J. Appl. Phys. 92 (2002) 3056 - 3064

M. de Ridder et al., Solid State Ionics 156 (2003) 255 - 262

# Fuel Cells

ionTOF

Yttria stabilized Zirconia (YSZ) after calcination



Calcination for 5 hours  
at 1000°C in an  
oxygen flow of 1.5 bar.



Segregation of  
monolayer of  
impurities

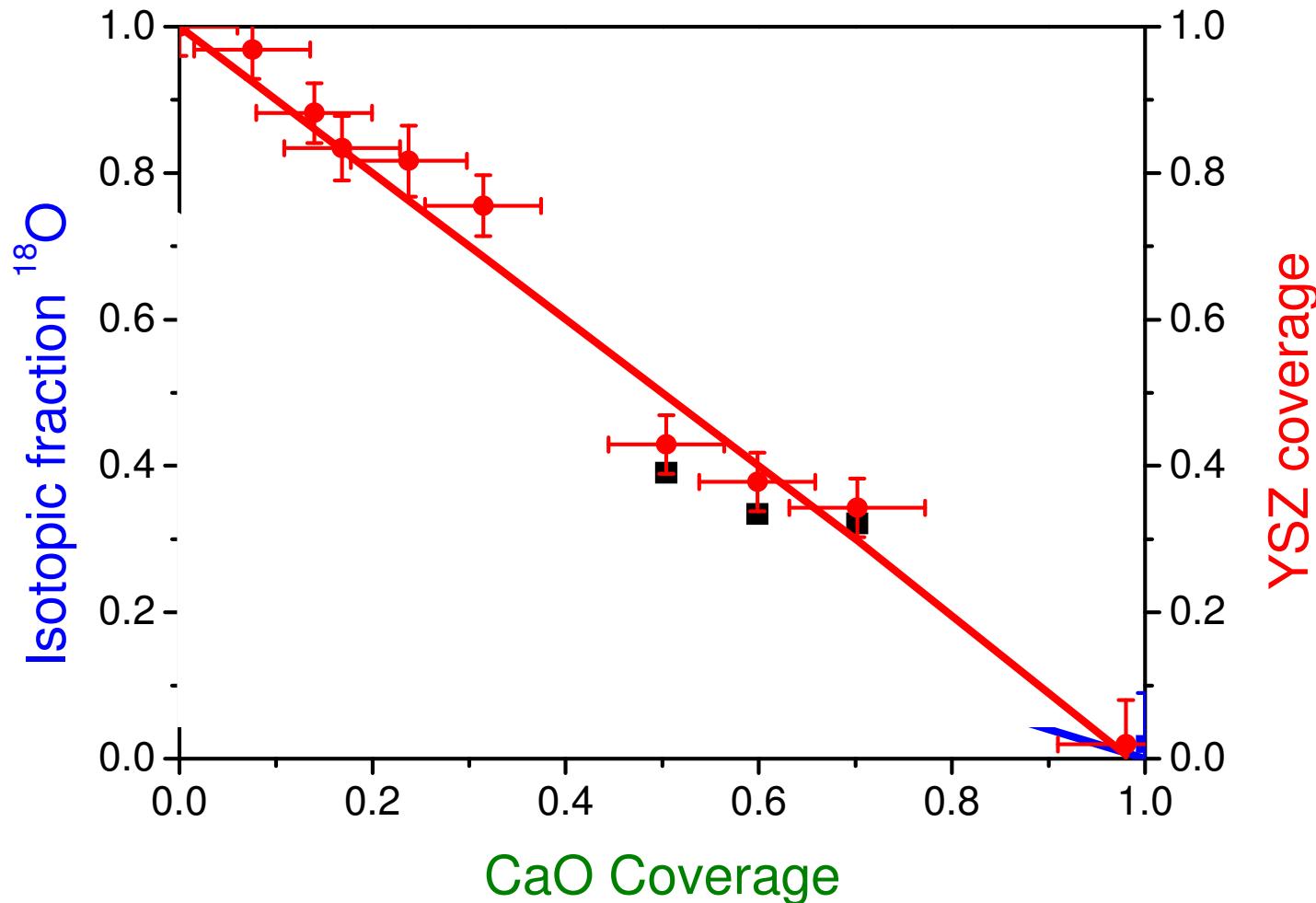
For T > 700 C: No Y, Zr in 1<sup>st</sup> atom !

XPS: Ca not visible ( ↔ Zr )

# Fuel Cells

ionTOF

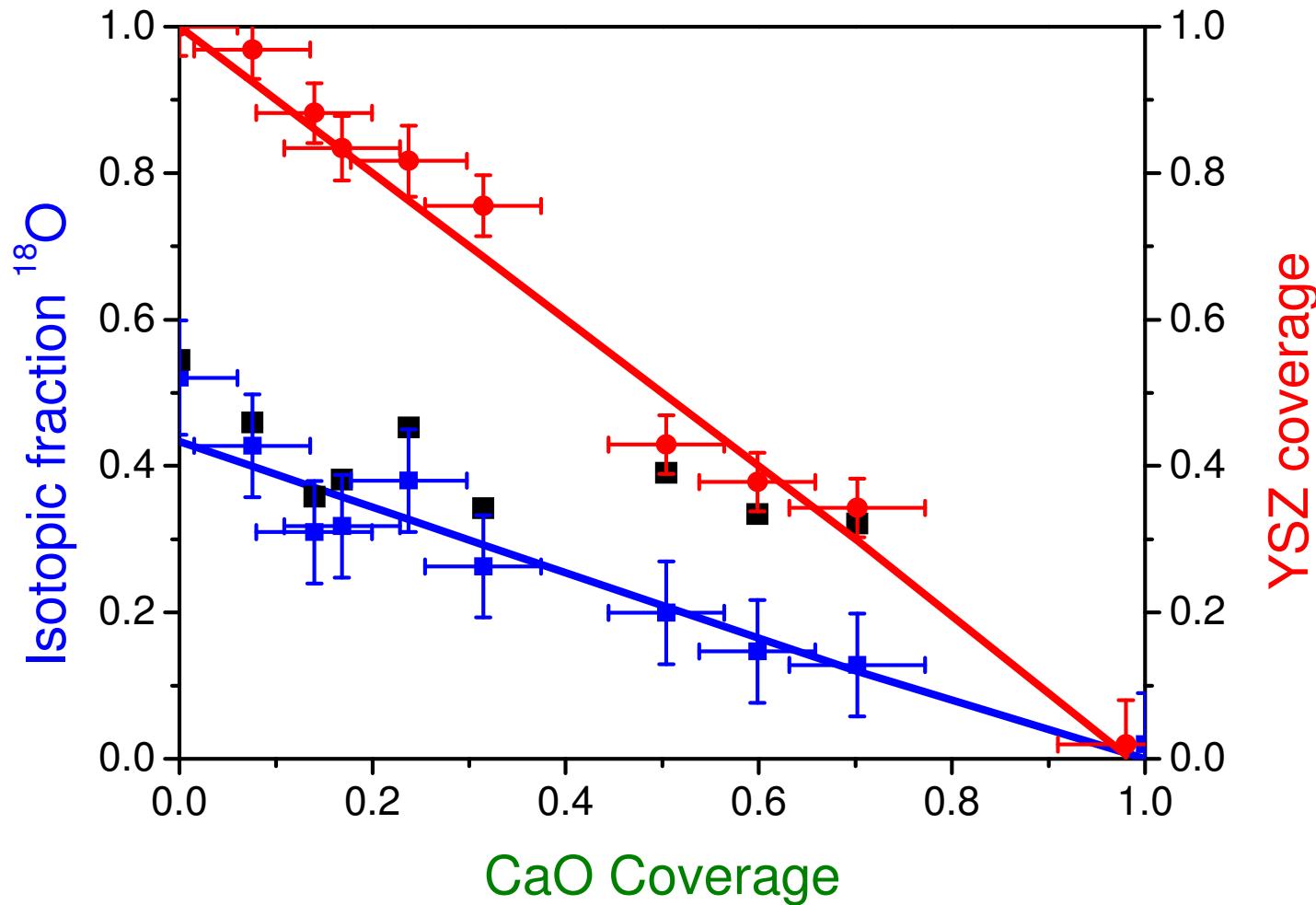
CaO coverage blocks  $^{16}\text{O} - ^{18}\text{O}$  exchange



# Fuel Cells

ionTOF

CaO coverage blocks  $^{16}\text{O} - ^{18}\text{O}$  exchange



# Coke Formation on Commercial TWC

ionTOF

Three Way Catalyst (TWC) ( Pt, Rh / CeO<sub>2</sub> /  $\gamma$  - Al<sub>2</sub>O<sub>3</sub> )

Cold start: 50% loss of Pt signal — *sintering or coke formation ?*

Room temperature oxidation with atomic oxygen gives complete recovery of Pt signal → *loss is due to coke.*

**Detection of C with “any” surface technique.**

**But: WHERE is the coke ??!**

**LEIS determines which fraction of Pt is covered by coke !**

## Applications:

- Number of Pt atoms available for catalysis.  
**Quality control of catalysts !**
- Detection of nucleation site for coke (active phase, support, binder, ... )

Diameter  $\longleftrightarrow$  TON; size often related to failure

## TEM:

- excellent catalyst characterisation
- detailed info, but local
- contrast required ( high Z cluster on low Z support )

## Chemisorption:

- requires known probe / surface interaction

## HS - LEIS:

- new technique; any material; clusters: 1 atom - 10 nm

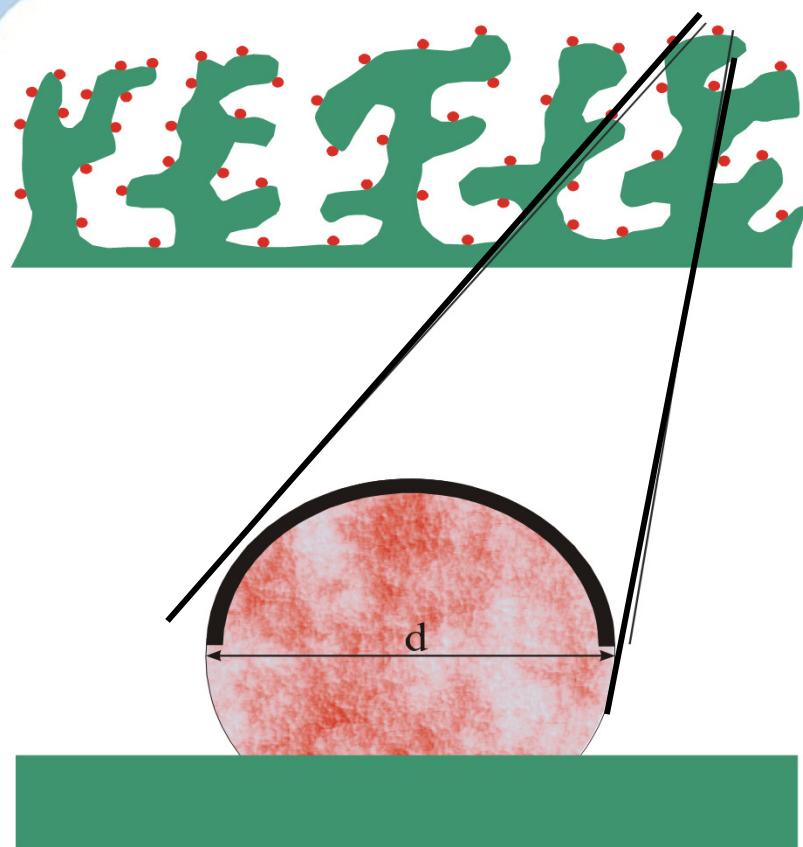
**Comparison:**  Richard A. P. Smith (J&M), ECASIA 2009

 T. Tanabe et al. (Toyota), Appl. Catal. A370 (2009) 108

# Important / unique applications for catalysis

ionTOF

## 4. Nanoclusters



- Average diameter nanoclusters
- Surface segregation in alloy clusters
- Core/shell particles  
(verification, closure, thickness shell)

**Example:** Three-Way catalyst (exhaust)

Pt clusters on  $\text{CeO}_2$ / ...../  $\gamma$ -alumina

Loading = 0.004 g Pt /  $\gamma$ -alumina

Cluster diameter: 1.6 nm (average)

Accurate for  $d < 10$  nm

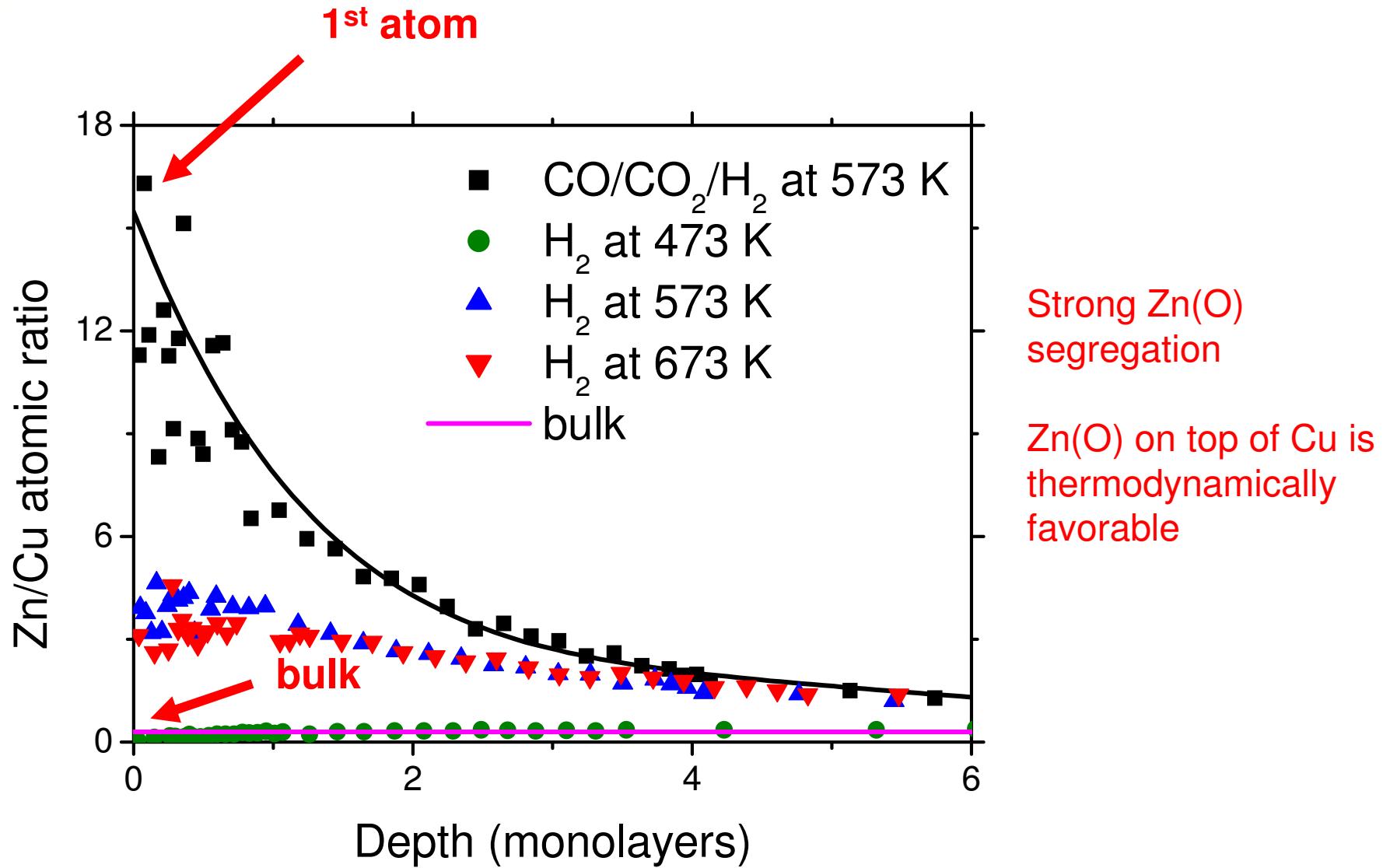
The diameter is derived from the ratio of the bulk loading (volume) to the LEIS signal (surface area)

*This method is possible where TEM fails* ( $d \leq 2$  nm; high Z support)

# Cu / ZnO / SiO<sub>2</sub> Catalysts

ionTOF

## Synthesis of Methanol, Fatty Acids



Oxidation states Cu and Zn in outer surface ?

ionTOF

LEIS + chemical titration !

XPS:

Oxidation states, **BUT** averaged over 10 – 20 atomic layers.

LEIS:

Elemental composition outer atomic layer, **BUT** no chemical info

Oxidation of metallic Cu, Zn gives shielding by oxygen.

Signal decrease: factor 5 resp. 3.7.

Chemical titration:

Information on oxidation states, **BUT** not only the outer surface (?)



? ? ?

# Oxidation states Cu and Zn in outer surface ?

ionTOF

LEIS + chemical titration !

XPS:

Oxidation states, **BUT** averaged over 10 – 20 atomic layers.

LEIS:

Elemental composition outer atomic layer, **BUT** no chemical info

Oxidation of metallic Cu, Zn gives shielding by oxygen.

Signal decrease: factor 5 resp. 3.7.

Chemical titration:

Information on oxidation states, **BUT** not only the outer surface (?)

LEIS + Chemical titration:



**oxidation states  
in the outer surface !**

- N<sub>2</sub>O for oxidation
- LEIS for detection increase in shielding after N<sub>2</sub>O treatment

# Cu / ZnO / SiO<sub>2</sub> - Catalyst

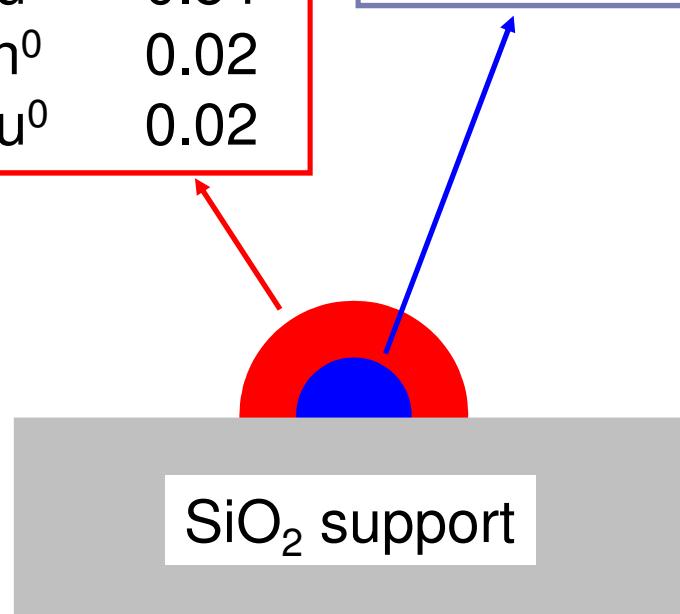
ionTOF

## Determination of cluster size and oxidation states by LEIS

### Cu/Zn/SiO<sub>2</sub> reduced at 473 K

Outermost atomic layer:	
ZnO	0.42
Cu <sup>1+</sup>	0.54
Zn <sup>0</sup>	0.02
Cu <sup>0</sup>	0.02

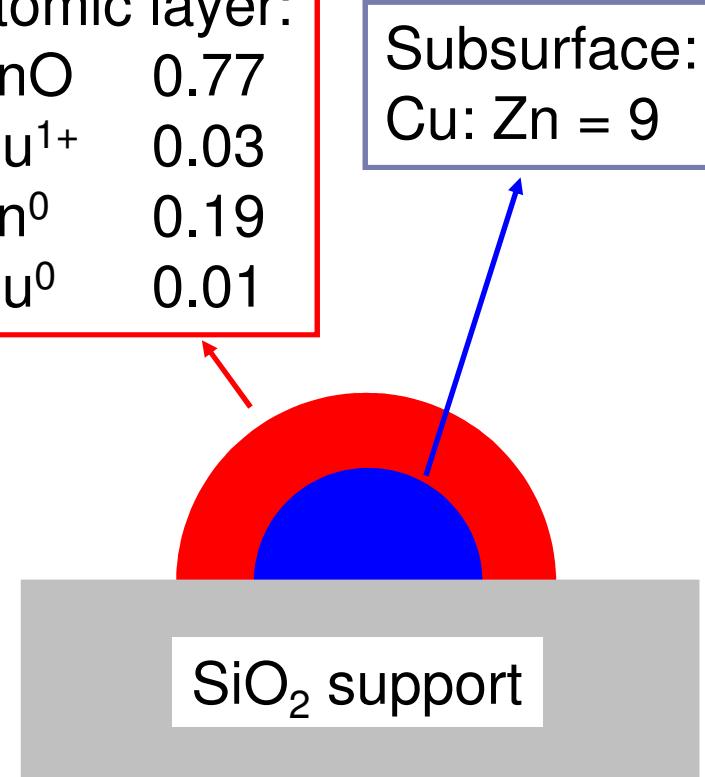
Subsurface:  
Cu: Zn = 9



### Cu/Zn/SiO<sub>2</sub> reduced at 673 K

Outermost atomic layer:	
ZnO	0.77
Cu <sup>1+</sup>	0.03
Zn <sup>0</sup>	0.19
Cu <sup>0</sup>	0.01

Subsurface:  
Cu: Zn = 9



## Atomic Layer Deposition (ALD)

“Growth with Digital Accuracy”

# How many cycles for Closure ?

ionTOF

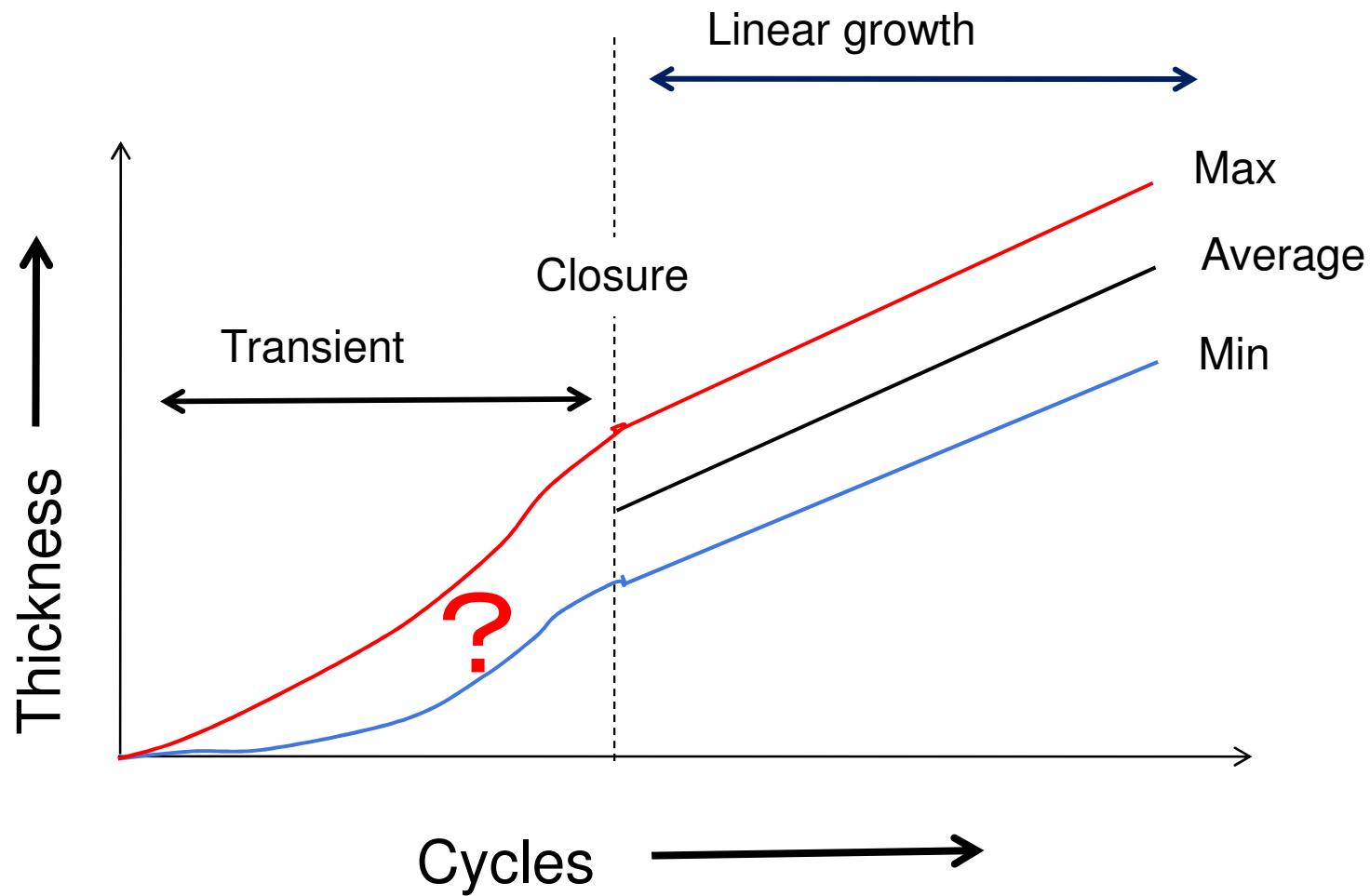
**ALD cartoons:** (often) show closed layer after 1 cycle  
**In practice:** closure after a few up to > 100 cycles !

**Typical examples** (depending on ALD conditions ! ):

- 6 cycles CrO<sub>x</sub> / Al<sub>2</sub>O<sub>3</sub>
- 6-9 cycles HfO<sub>2</sub> / Si
- ~ 15 cycles AlN / SiO<sub>2</sub>
- ~ 40 cycles Al<sub>2</sub>O<sub>3</sub> / Si
- ~ 70 cycles Fe<sub>2</sub>O<sub>3</sub> / ZrO<sub>2</sub>
- ~ 150 cycles TiN / SiO<sub>2</sub>

# Layer thickness versus cycle #

ionTOF



The transient regime determines closure and uniformity

# **Characterization of MOCVD vs. ALD HfO<sub>2</sub> layer closure and growth mode on Silicon: a new model for preferential deposition**

M.J.P. Hopstaken<sup>1</sup>, M.S. Gordon<sup>1</sup>, J. Schaeffer<sup>2</sup>, H. Jagannathan<sup>1</sup>,  
T. Grehl<sup>3</sup>, H.H. Brongersma<sup>3,4</sup>, M. Copel<sup>1</sup>, M.M. Frank<sup>1</sup>, V. Narayanan<sup>1</sup>,  
K. Choi<sup>2</sup>, M. Fartmann<sup>4</sup>, D. Breitenstein<sup>4</sup>

<sup>1</sup>IBM Research, <sup>2</sup>GLOBALFOUNDRIES, <sup>3</sup>ION -TOF, <sup>4</sup>Tascon

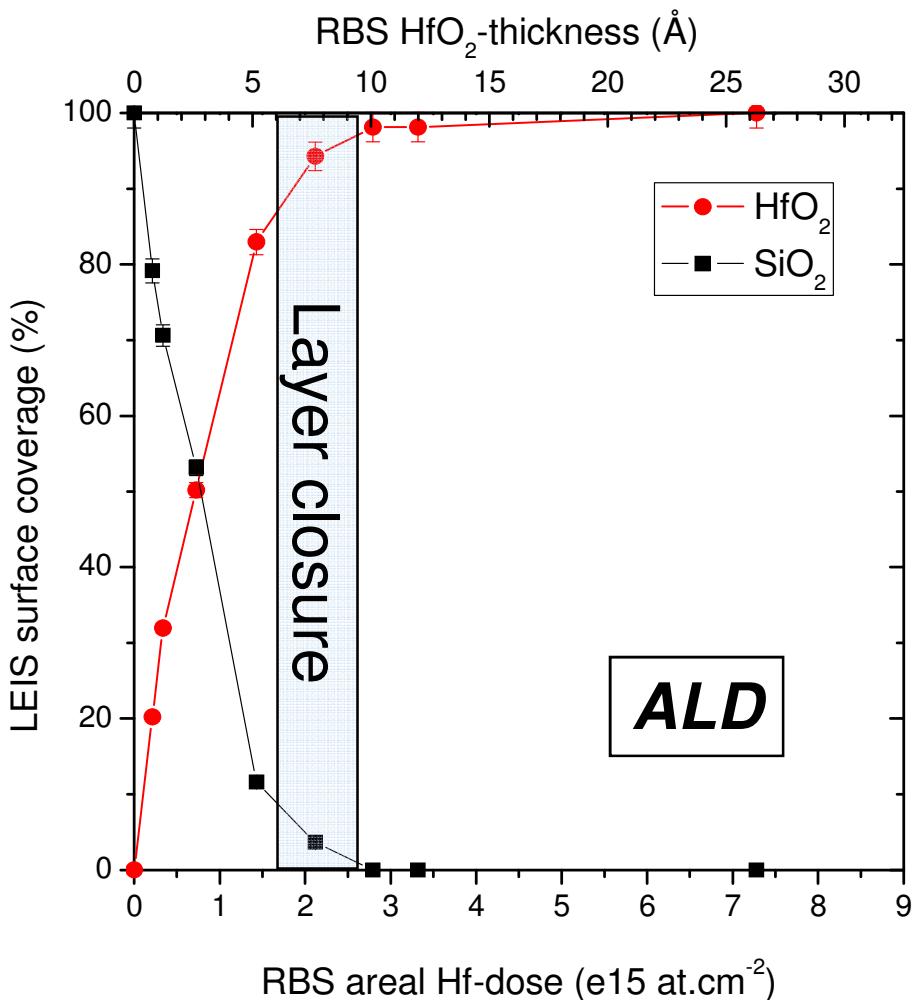
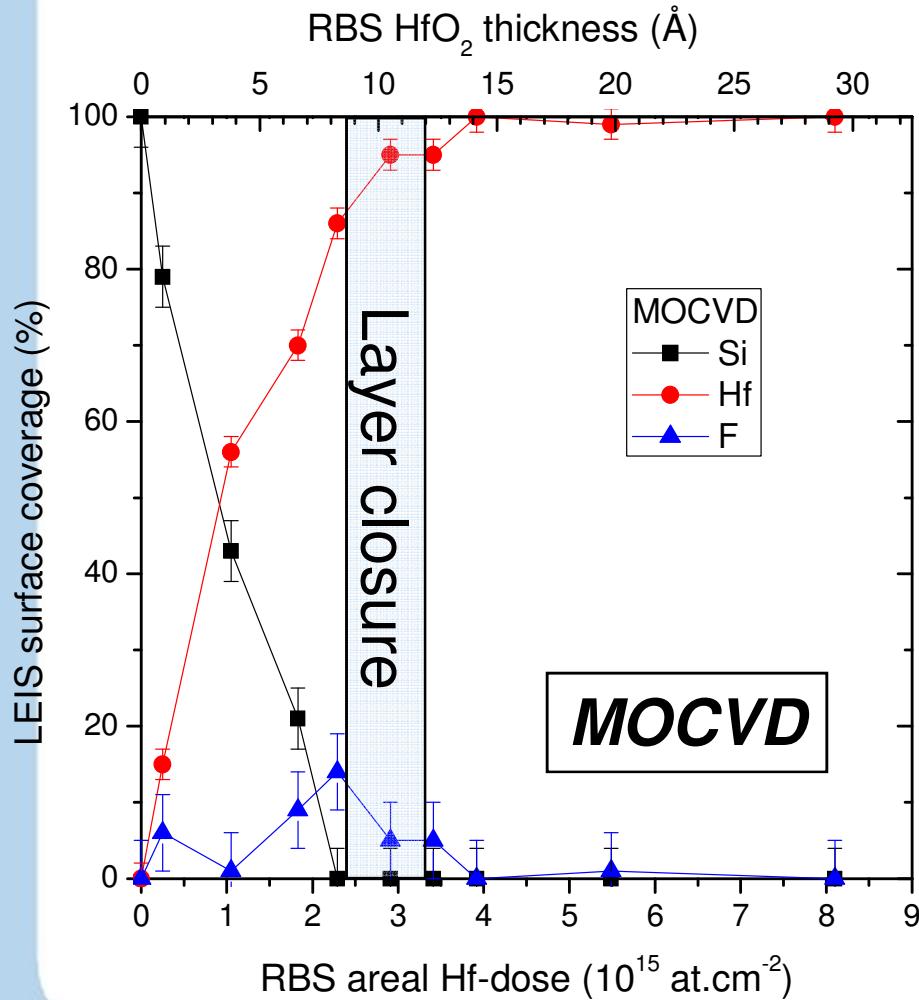
ALD 2010, June 21 – 23, 2010 Seoul, Korea

# $\text{HfO}_2$ layer closure: MOCVD vs ALD

ionTOF

Surface fractions (LEIS) as function of coverage

Earlier layer closure for ALD- $\text{HfO}_2$



# LEIS and Growth



- Initial growth; growth mode
- Poisoning, activation
- Closure, pinholes
- Thickness distribution

*Conclusion IBM / Global Foundries / ION-TOF / Tascon study:*

- Origin of the superior quality of the ALD grown layers revealed by HS-LEIS  
( other analytic tools have insufficient depth resolution )

# Summary: Why do you need LEIS ?? !!

- Any material, any T
- Quantitative
- 1<sup>st</sup> atom and high-resolution in-depth !!

## **Unique applications of High Sensitivity LEIS ( NOT's )**

- Segregation, Anti-wetting
- Adhesion: “ 5% vs 100% ”
- Follow ultrathin growth
- Pinholes in ultrathin; Nano pinholes
- Metal / polymer in-depth diffusion
- Catalysis: poison, promoter, probe molecules, core-shell, .....
- Nanoclusters (diameter; outer atoms)
- Inorganics: oxidation states
- Improve cleaning strategies

Complementarity to XPS, ToF-SIMS, .....

# Miscellaneous applications



- Microelectronics, polymers, ceramics, catalysis, sensors, .....

## But also:

- Pinholes in coatings
- Candy wrappers
- Gold mining
- F 16 Dome
- Bone tissue, implants, stents, .....
- Ageing of Linoleum ( “ Linowonder” )
- Anti-wetting (watches, .....)
- Floor wax

# Complementary Cutting Edge techniques

HS-LEIS

Qtac<sup>100</sup>

HR-XPS

Scienta ESCA 300



*Lehigh University*



qtac<sup>100</sup>

Thank you for your attention.